

ATMOSPEC

DARLINGTON COMPLEMENTARY SILICON POWER TRANSISTORS

...designed for general-purpose amplifier and low speed switching applications

FEATURES:

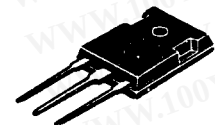
- * Collector-Emitter Sustaining Voltage-
 $V_{CE(sus)} = 60 \text{ V (Min) - TIP140, TIP145}$
 $= 80 \text{ V (Min) - TIP141, TIP146}$
 $= 100 \text{ V (Min) - TIP142, TIP147}$
- * Collector-Emitter Saturation Voltage
 $V_{CE(sat)} = 2.0 \text{ V (Max.) @ } I_C = 5.0 \text{ A}$
- * Monolithic Construction with Built-in Base-Emitter Shunt Resistor

NPN	PNP
TIP140	TIP145
TIP141	TIP146
TIP142	TIP147

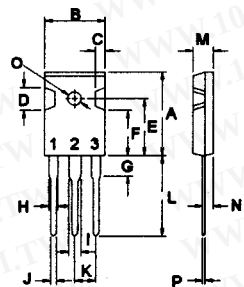
10 AMPERE
 DARLINGTON
 COMPLEMENTARY SILICON
 POWER TRANSISTORS
 60-100 VOLTS
 125 WATTS

MAXIMUM RATINGS

Characteristic	Symbol	TIP140 TIP145	TIP141 TIP146	TIP142 TIP147	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	100	V
Collector-Base Voltage	V_{CBO}	60	80	100	V
Emitter-Base Voltage	V_{EBO}	5.0			V
Collector Current-Continuous -Peak	I_C I_{CM}	10 15			A
Base Current	I_B	0.5			A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	125 1.0			W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{STG}	- 65 to +150			$^\circ\text{C}$



TO-247(3P)



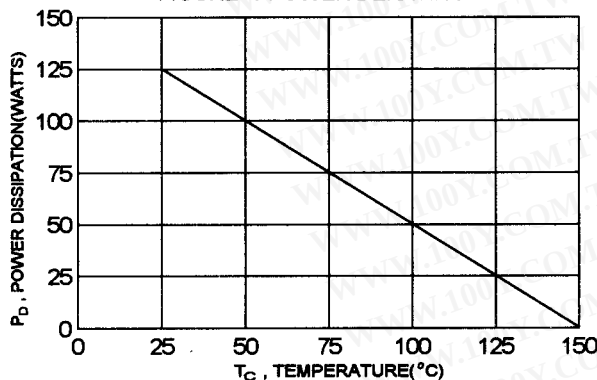
PIN 1.BASE
 2.COLLECTOR
 3.EMITTER

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	1.0	$^\circ\text{C/W}$

DIM	MILLIMETERS	
	MIN	MAX
A	20.63	22.38
B	15.38	16.20
C	1.90	2.70
D	5.10	6.10
E	14.81	15.22
F	11.72	12.84
G	4.20	4.50
H	1.82	2.46
I	2.92	3.23
J	0.89	1.53
K	5.28	5.66
L	18.50	21.50
M	4.68	5.36
N	2.40	2.80
O	3.25	3.65
P	0.55	0.70

FIGURE -1 POWER DERATING



TIP140, TIP141, TIP142 NPN / TIP145, TIP146, TIP147 PNP

ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector - Emitter Sustaining Voltage (1) ($I_C = 30\text{ mA}$, $I_B = 0$) TIP140, TIP145 TIP141, TIP146 TIP142, TIP147	$V_{CE(sus)}$	60 80 100		V
Collector Cutoff Current ($V_{CE} = 30\text{ V}$, $I_B = 0$) ($V_{CE} = 40\text{ V}$, $I_B = 0$) ($V_{CE} = 50\text{ V}$, $I_B = 0$) TIP140, TIP145 TIP141, TIP146 TIP142, TIP147	I_{CEO}		2.0 2.0 2.0	mA
Collector Cutoff Current ($V_{CB} = 60\text{ V}$, $I_E = 0$) ($V_{CB} = 80\text{ V}$, $I_E = 0$) ($V_{CB} = 100\text{ V}$, $I_E = 0$) TIP140, TIP145 TIP141, TIP146 TIP142, TIP147	I_{CBO}		1.0 1.0 1.0	mA
Emitter Cutoff Current ($V_{EB} = 5.0\text{ V}$, $I_C = 0$)	I_{EBO}		2.0	mA

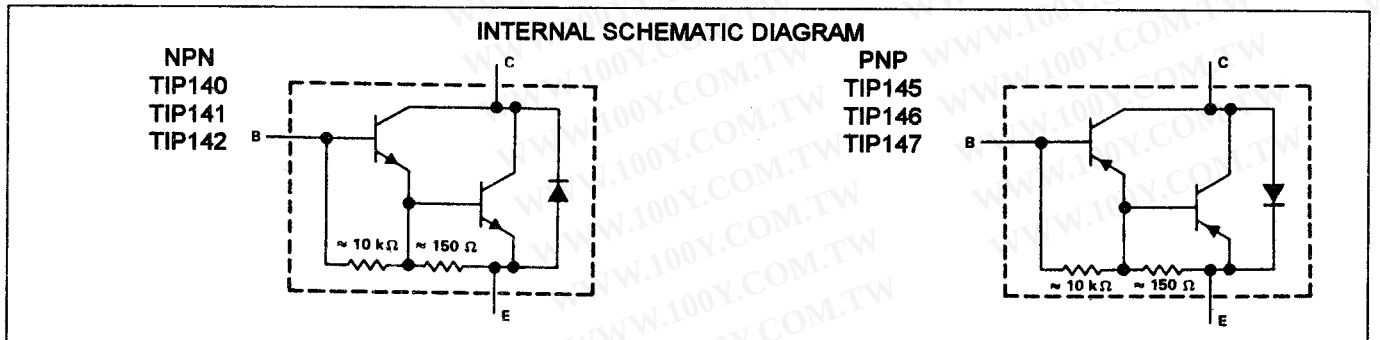
ON CHARACTERISTICS (1)

DC Current Gain ($I_C = 5.0\text{ A}$, $V_{CE} = 4.0\text{ V}$) ($I_C = 10\text{ A}$, $V_{CE} = 4.0\text{ V}$)	h_{FE}	1000 500		
Collector-Emitter Saturation Voltage ($I_C = 5.0\text{ A}$, $I_B = 10\text{ mA}$) ($I_C = 10\text{ A}$, $I_B = 40\text{ mA}$)	$V_{CE(sat)}$		2.0 3.0	V
Base-Emitter Saturation Voltage ($I_C = 10\text{ A}$, $I_B = 40\text{ mA}$)	$V_{BE(sat)}$		3.5	V
Base-Emitter On Voltage ($I_C = 10\text{ A}$, $V_{CE} = 4.0\text{ V}$)	$V_{BE(on)}$		3.0	V

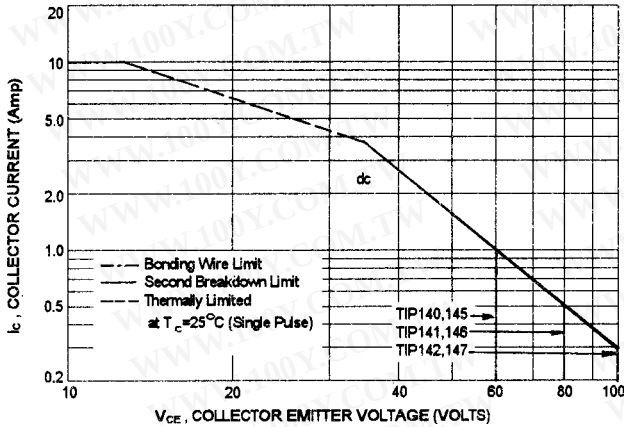
SWITCHING CHARACTERISTICS

Delay Time	$V_{CC} = 30\text{ V}$, $I_C = 5.0\text{ A}$ $I_{B1} = -I_{B2} = 20\text{ mA}$, $t_p = 20\mu\text{s}$, Duty Cycle $\leq 2.0\%$	t_d	0.15(Typ)		μs
Rise Time		t_r	0.55(Typ)		μs
Storage Time		t_s	2.5(Typ)		μs
Fall Time		t_f	2.5(Typ)		μs

(1) Pulse Test: Pulse width = $300\mu\text{s}$, Duty Cycle $\leq 2.0\%$



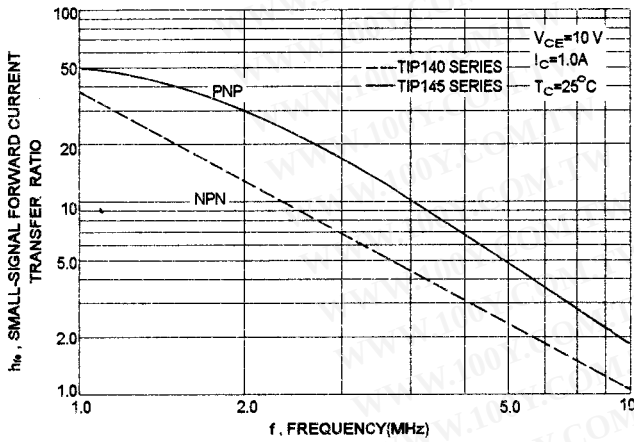
ACTIVE REGION SAFE OPERATING AREA (SOA)



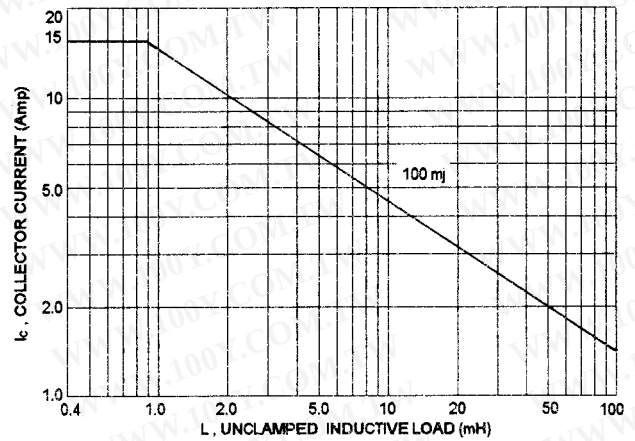
There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate I_c - V_{ce} limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of SOA curve is base on $T_{J(PK)} = 150^\circ\text{C}$; T_c is variable depending on conditions. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

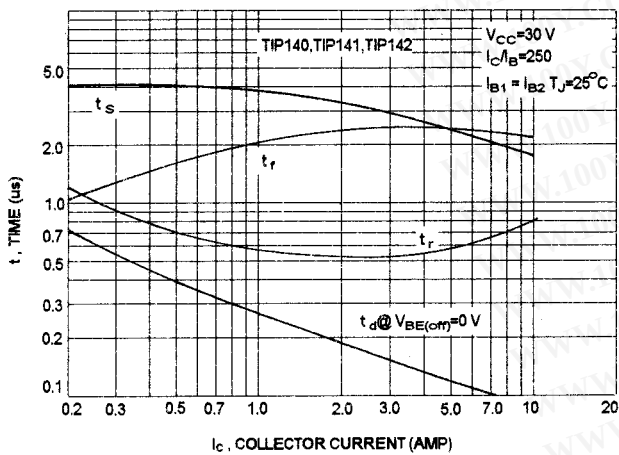
SMALL-SIGNAL COMMON-EMITTER FORWARD CURRENT TRANSFER RATIO



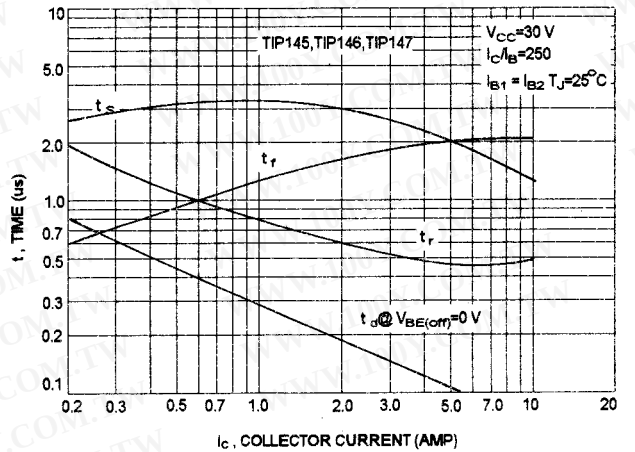
UNCLAMPED INDUCTIVE LOAD



SWITCHING TIME

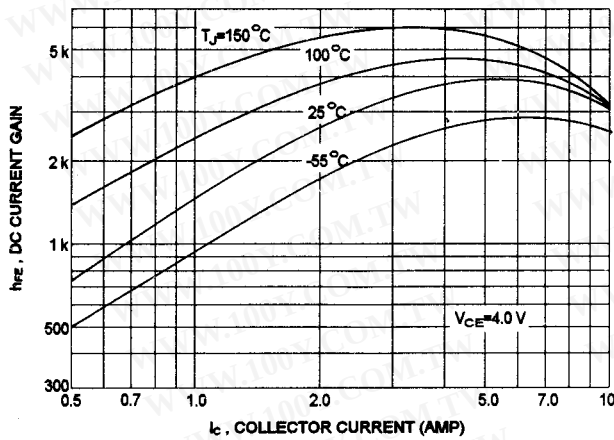


SWITCHING TIME



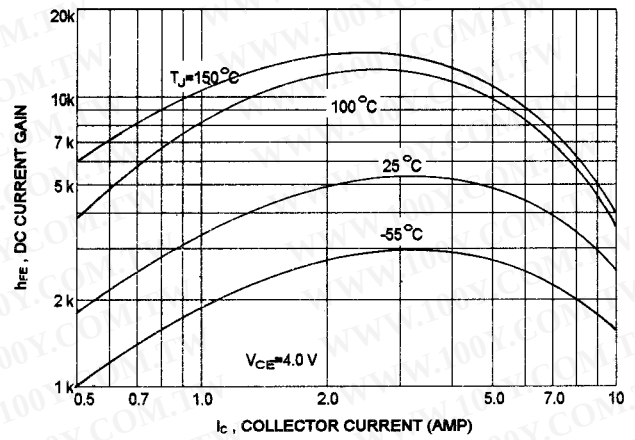
NPN TIP140, TIP141, TIP142

DC CURRENT GAIN

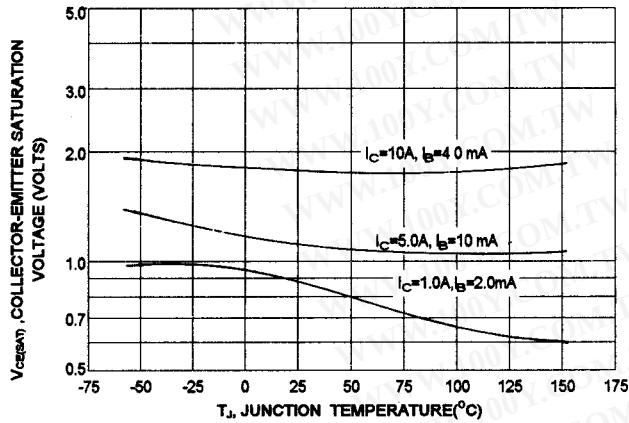


PNP TIP145, TIP146, TIP147

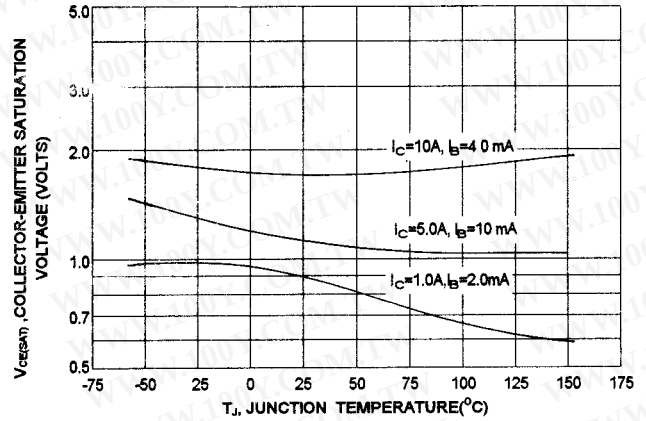
DC CURRENT GAIN



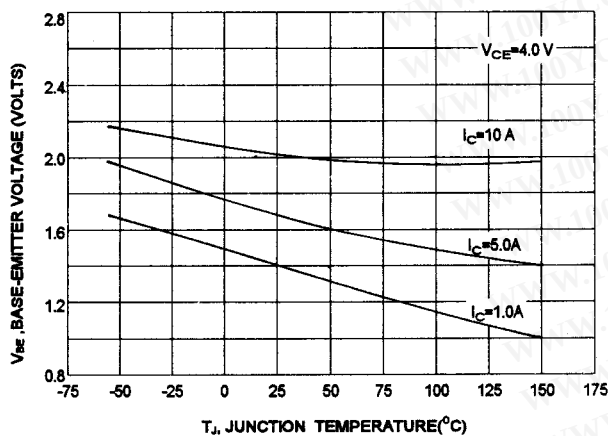
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR-EMITTER SATURATION VOLTAGE



BASE-EMITTER VOLTAGE



BASE-EMITTER VOLTAGE

